NSH010N10T

N-Channel Enhanced Shielded Gate Trench Power MOSFET

Pb-Free RoHS COMPLIANT

Voltage:	100	Volts	**Current:**	385	Amperes	**Package:**	TOLL

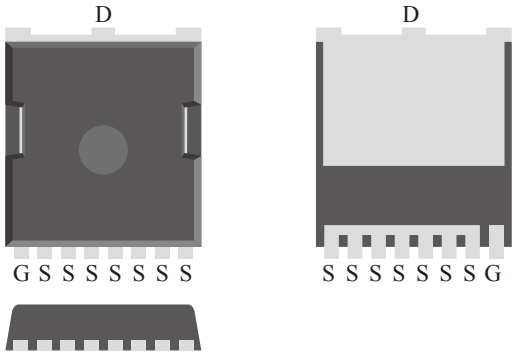
Features

- NH'S Advanced SGT Technology
- Low Reverse Transfer Capacitances
- Low Gate Charge For Low Switching Loss
- Excellent Qg*Rds(on) Product(FOM）

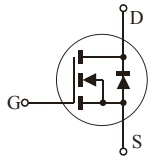
Typical Applications

- Synchronous Rectification
- High-Frequency Circuits
- The Motor Drives
- Automotive Electronics

Diagram:



Polarity:



Product Summary

VDS Min.@T_j	100	**V**
I_D Min.@Ta	385	**A**
RDS(ON)(TYP)@10V	1.05	**mΩ**

***100% UIS TESTED**

***100% ΔVDS TESTED**

Absolute Maximum Ratings (Ta=25℃ Unless Otherwise Specified)

Parameter	Test Conditions	Symbol	Ratings	Unit
Drain-Source Voltage		V_{DS}	100	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current (Note 1)	Ta= 25 ℃ Ta= 100 ℃	I_D	385 246	A
Drain Current-Pulse (Note 1)	T_J< 150 ℃	I_{DM}	1540	A
Maximum Power Dissipation Power Dissipation Derating Factor Above 25℃	Ta= 25 ℃ Ta= 100 ℃	P_D	417 167	W
Derating Factor		D_F	3.33	W/℃
Avalanche Current,Single Pulse (Note 1)	L= 0.5 mH	I_{AS}	87	A
Single Pulse Avalanche Energy (Note 1) Test Circuit & Waveform See Fig.17	L= 0.5 mH IAS= 87 A,RG= 10.0 Ω Starting Tj=25 ℃,VG = 10.0 V	E_{AS}	1901	mJ

Thermal Characteristcs (Ta=25℃ Unless Otherwise Specified)

Parameter	Test Conditions	Symbol	Typ.	Unit
Junction Temperature		T_J	-55 to 150	℃
Storage Temperature Range		T_{STD}	-55 to 150	℃
Thermal Resistance Junction To Ambient With Steady-State	Still Air Environment With Ta=25℃	$R_{\theta JA}$	42	℃/W
Thermal Resistance Junction-Case With Steady-State	Device Mounted On 1 in2 FR-4 Board With 2oz. Copper	$R_{\theta JC}$	0.3	

Notes: 1.Pulse Width Limited By Max. Junction Temperature. (See Fig.14)

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Electrical Characteristcs (Ta=25℃ Unless Otherwise Specified)

Parameter	Test Conditions	Symbol	Min.	Typ.	Max.	Unit
Static Off Characteristics						
Drain-Source Breakdown Voltage	VGS=0V,ID=250uA	BV_{DSS}	100	--	--	V
Bvdss Temperature Coefficient	ID=250uA,Reference25℃	$\Delta BV_{DSS}/\Delta T_J$	--	0.11	--	V/℃
Drain-Source Leakage Current	VDS= 100 V,VGS=0V	I_{DSS}	--	--	1	uA
Gate-Body Leakage Current	VGS= ±20 V,VDS=0V	I_{GSS}	--	--	±100	nA
Forward Transconductance	ID= 20.0 A,VDS= 5 V	gfs	--	325	--	S
Static On Characteristics						
Gate Threshold Voltage	VGS= VDS ID=250uA	$V_{GS(TH)}$	2.5	3.3	4.1	V
Drain-Source On Resistance	ID= 20.0 A,VGS= 10.0 V	$R_{DS(ON)}$	--	1.05	1.2	mΩ
	ID= 20.0 A,VGS= 5.0 V		--	1.52	1.8	
Dynamic Characteristics						
Gate Resistance	VGS=0V,VDS=0V, Freq.=1MHz	R_g	--	1.2	--	Ω
Input Capacitance	VDS= 50 V	C_{iss}	--	15812	--	pF
Output Capacitance	VGS= 0 V	C_{oss}	--	3394	--	pF
Reverse Transfer Capacitance	F= 1 MHZ	C_{rss}	--	128	--	pF
Switching Paramters With Inductive Load(Test Circuit & Waveform See Fig.15)						
Turn-On Delay Time	VDS= 50 V	$t_{d(on)}$	--	78.1	--	ns
Turn-On Rise Time	VGS= 10.0 V	t_r	--	102.3	--	ns
Turn-Off Delay Time	RG= 10.0 Ω	$t_{d(off)}$	--	45.2	--	ns
Turn-Off Rise Time	L= 0.5 mH	t_f	--	48	--	ns
Gate Charge Paramters (Test Circuit & Waveform See Fig.16)						
Total Gate Charge	VDS= 50 V	Q_g	--	256	--	nC
Gate-Source Charge	VGS= 10.0 V	Q_{gs}	--	82	--	nC
Gate-Drain Charge	ID= 20.0 A	Q_{gd}	--	71	--	nC
Drain-Source Diode Characteristics And Maximum Ratings (Test Circuit & Waveform See Fig.18)						
Max. Diode Forward Current		I_S	--	--	385.0	A
Max. Pulsed Forward Current		I_{SM}	--	--	1540	A
Diode Forward Voltage	ID= 20.0 A,VGS=0V	V_{SD}	--	0.8	1.4	V
Reverse Recovery Time	IS= 20.0 A,di/dt= 100 A/us	t_{rr}	--	105	--	ns
Reverse Recovery Charge	VGS= 0.0 V	Q_{rr}	--	258	--	nC
Reverse Recovery Current		I_{RRM}	--	5.0	--	A

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Typical Characteristics Curves

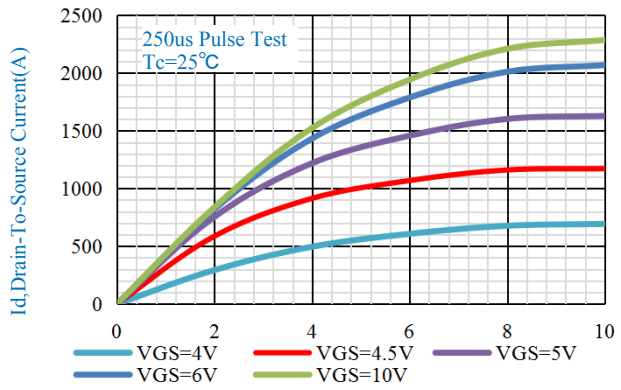


Fig.1-Output Characteristic

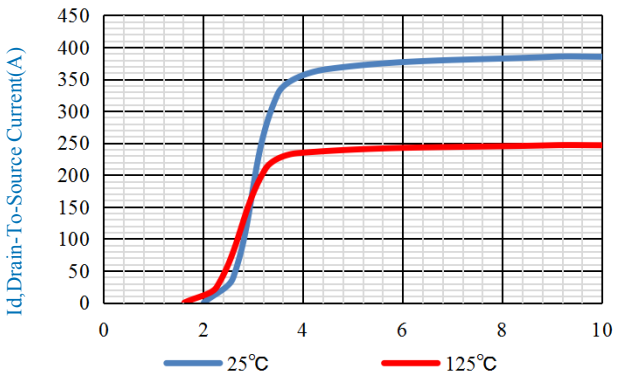


Fig.2-Transfer Characteristic

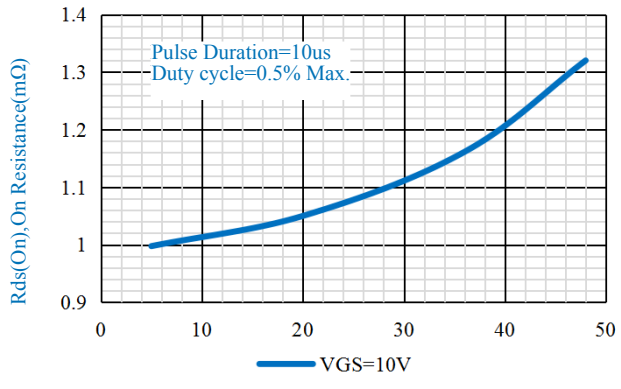


Fig.3-On Resistance Vs. Drain Current

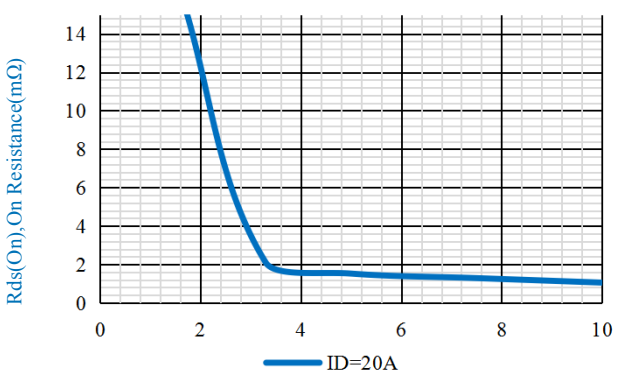


Fig.4-On Resistance Vs. Gate Source Voltage

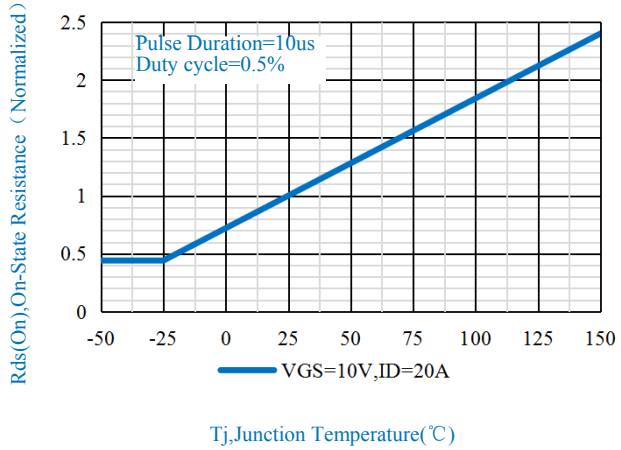


Fig.5-On Resistance Vs. Junction Temperature

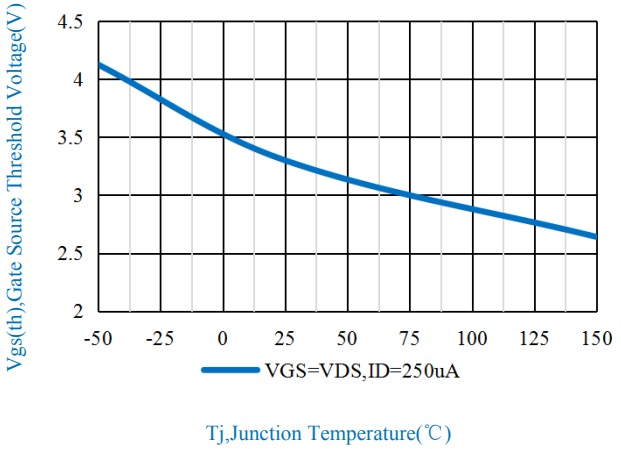


Fig.6-Gate Source Threshold Voltage Vs. Junction Temperature

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Typical Characteristics Curves

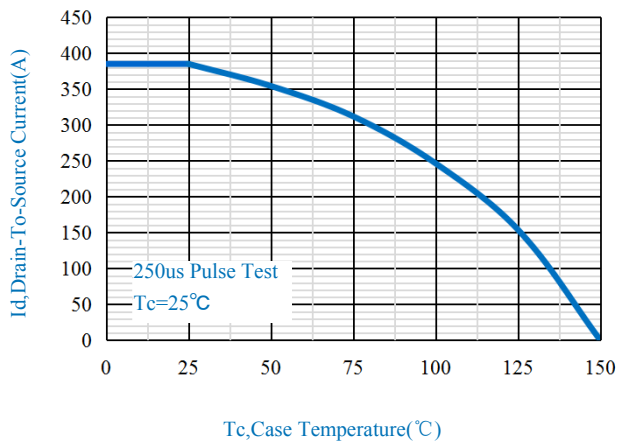


Fig.7-Maximum Continuous Drain Current Vs. Case Temperature

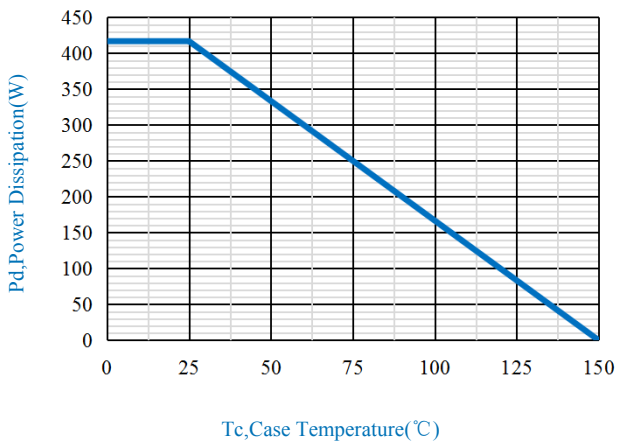


Fig.8-Maximum Power Dissipation Vs. Case Temperature

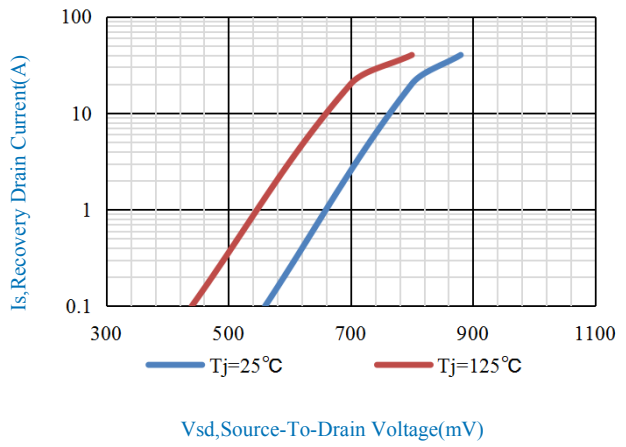


Fig.9-Source-To-Drain Diode Forward Voltage

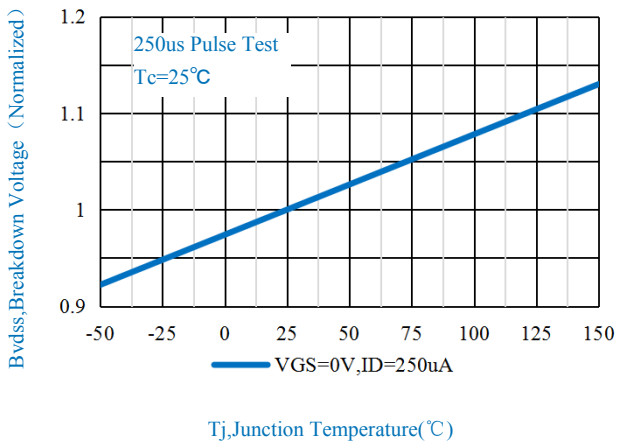


Fig.10-Breakdown Voltage Vs. Junction Temperature

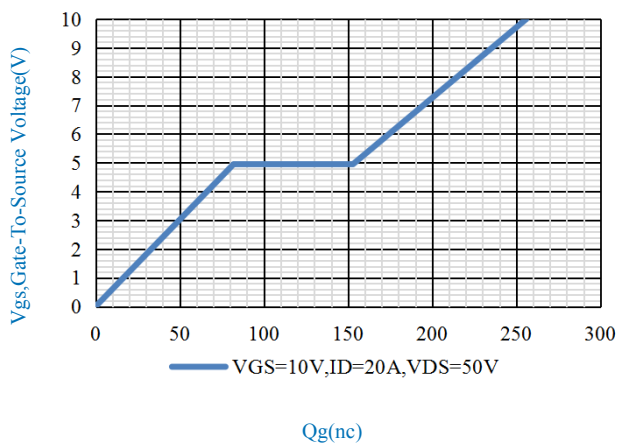


Fig.11-Gate Charge Waveform

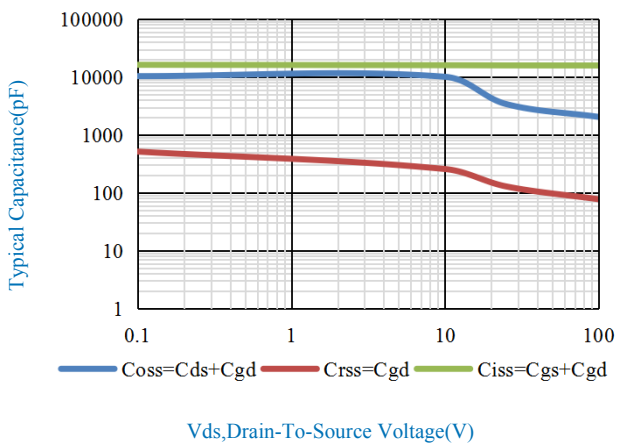


Fig.12-Typical Capacitance Vs. Drain-To-Source Voltage

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Typical Characteristics Curves

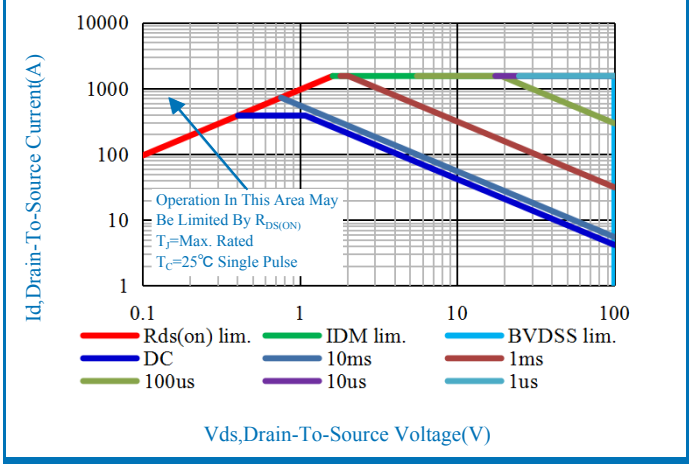


Fig.13-Maximum Safe Operating Area(SOA)

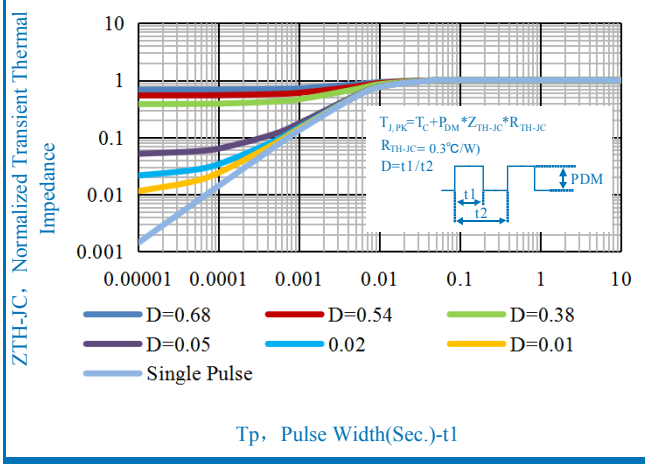
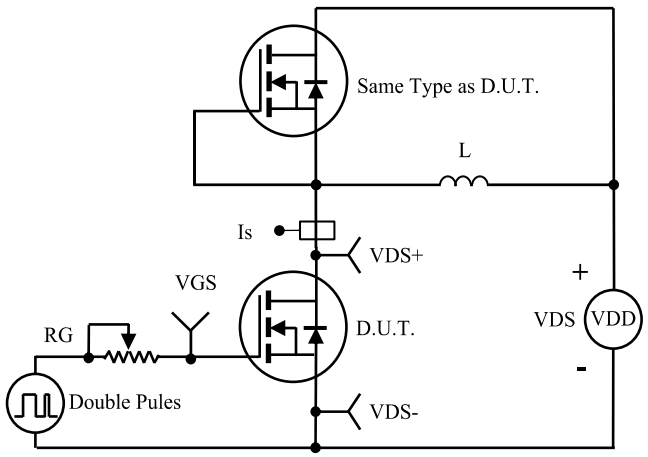


Fig.14- Normalized Maximum Transient Thermal Impedance Vs.Pulse Width

Inductive Load Test Circuit & Waveform



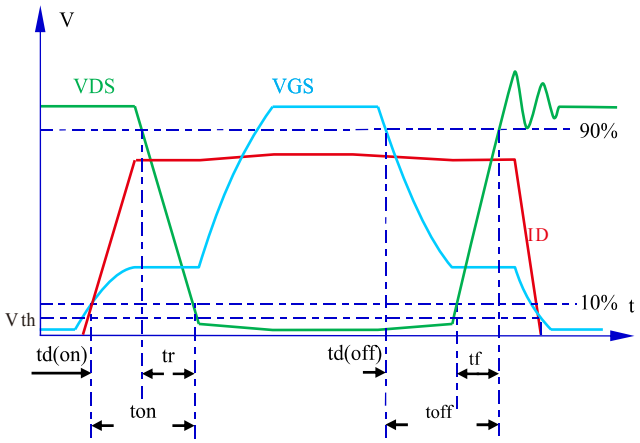


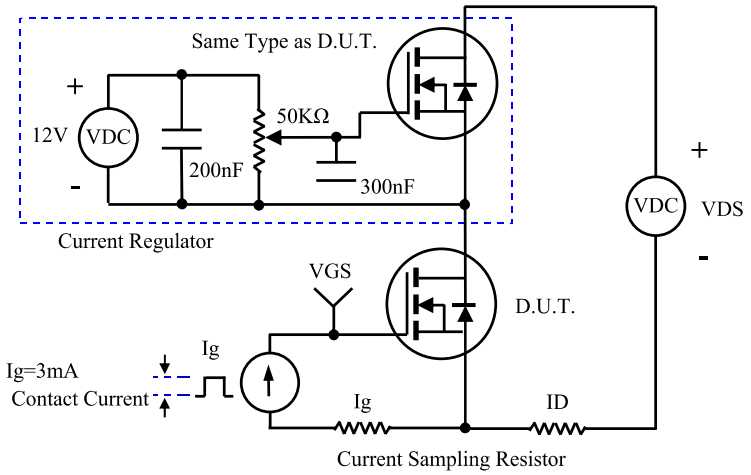
Fig.15- Inductive Switching Test Circuit & Waveform

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Test Circuit & Waveform



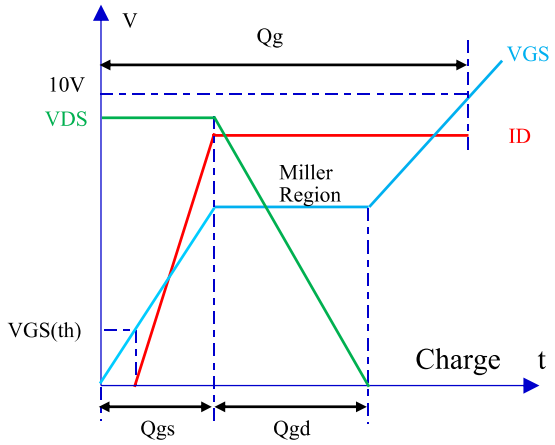
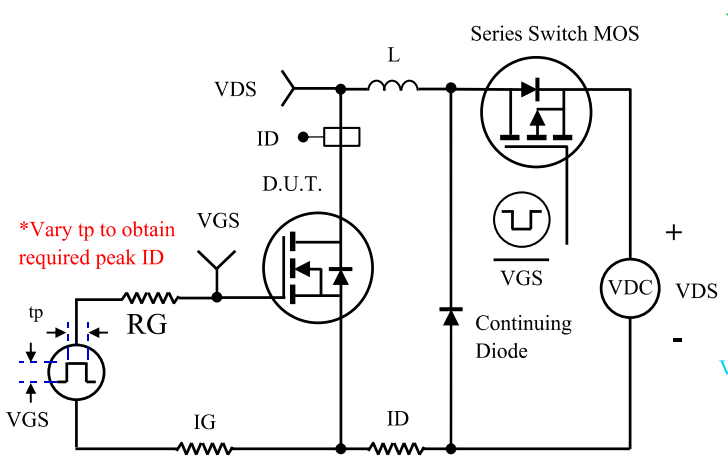


Fig.16-Gate Charge Test Circuit & Waveform



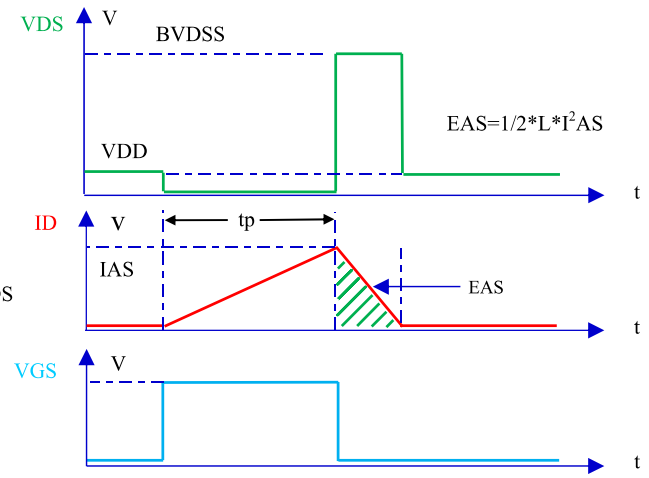
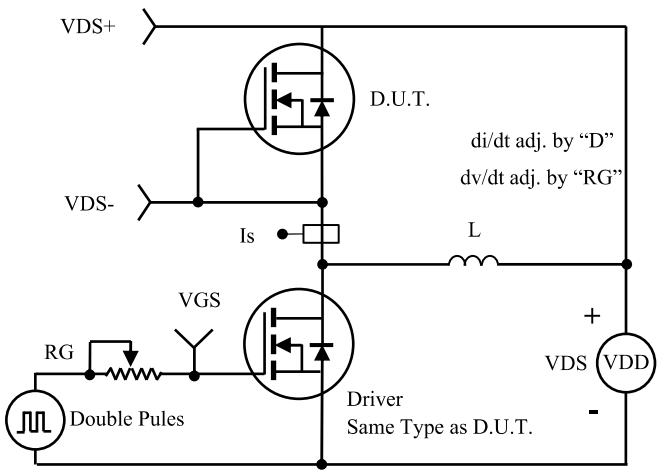


Fig.17- Unclamped Inductive Switching (UIS) Test Circuit & Waveform



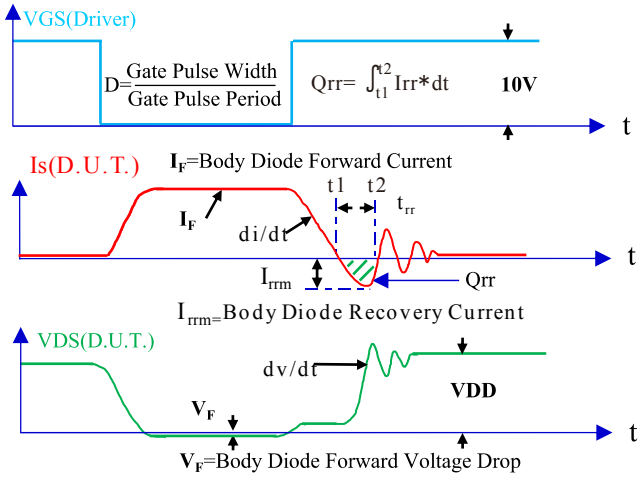


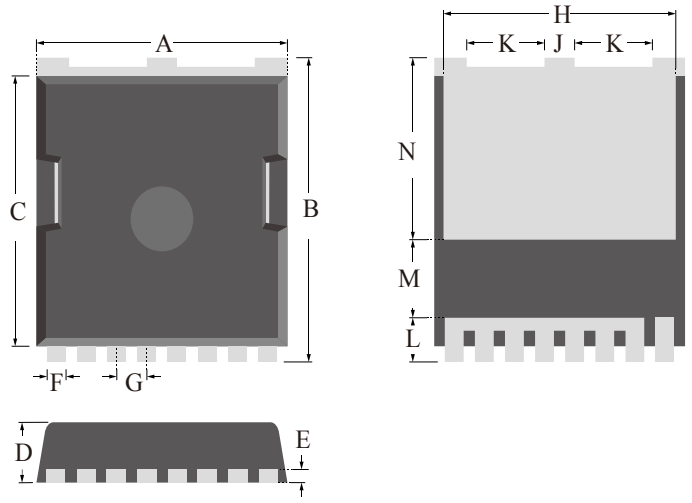
Fig.18- Diode Recovery Test Circuit & Waveform

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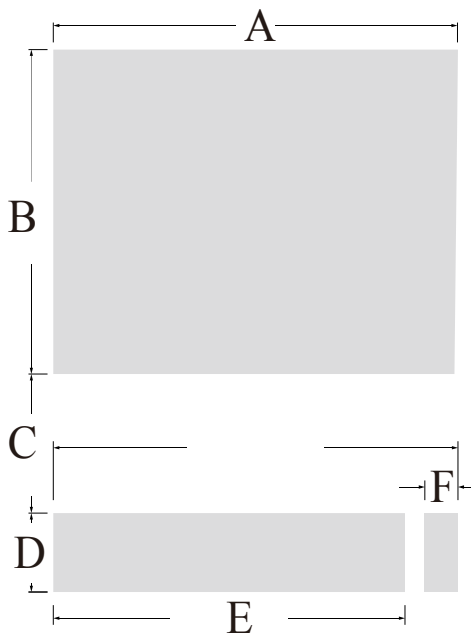
OUTLINE DRAWINGS



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OUTLINE DIMENSIONS						
Dim.	Milimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	9.65	-	10.15	0.3799	-	0.3996
B	11.45	-	11.95	0.4508	-	0.4705
C	10.15	-	10.65	0.3996	-	0.4193
D	2.20	-	2.40	0.0866	-	0.0945
E	0.35	-	0.65	0.0138	-	0.0256
F	0.65	-	0.85	0.0256	-	0.0335
G	1.05	-	1.35	0.0413	-	0.0531
H	7.95	-	8.45	0.3130	-	0.3327
J	1.10	-	1.30	0.0433	-	0.0512
K	3.00	-	3.20	0.1181	-	0.1260
L	1.55	-	1.85	0.0610	-	0.0728
M	2.85	-	3.15	0.1122	-	0.1240
N	6.85	-	7.15	0.2697	-	0.2815

RECOMMEDNED LAYOUT DRAWINGS



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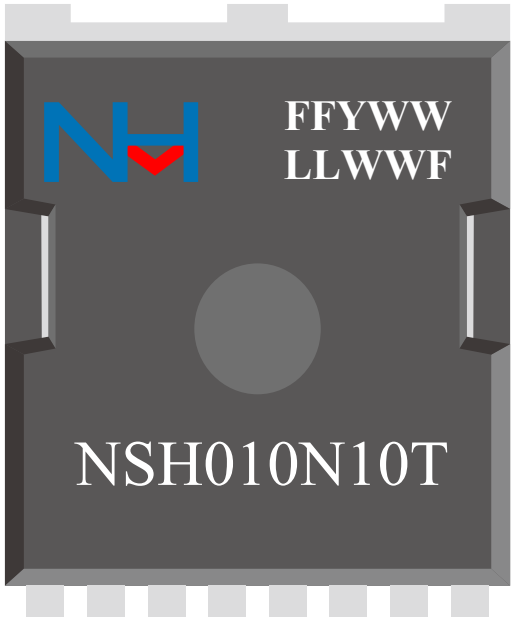
OUTLINE DIMENSIONS						
Dim.	Milimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	-	12.00	-	-	0.4724	-
B	-	10.00	-	-	0.3937	-
C	-	5.85	-	-	0.2303	-
D	-	2.50	-	-	0.0984	-
E	-	9.00	-	-	0.3543	-
F	-	1.00	-	-	0.0394	-

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MARKING



MARKING INSTRUCTION

NH=Niuhang Trademark

FF=Product Line Code,According To Actual Changes

YWW=Date Code,According To Actual Changes

LLWWF=Inernal Code,According To Actual Changes

NSH010N10T=Model

PACKING INFORMATION

Package Type	Package Code	Productor Weight Approx(g/Pcs)	Package Method	Quantity (Pcs/Min. Pack.)	Quantity (Pcs/Inner Box)	Quantity (Pcs/Carton)
TOLL	P1	0.742	Tape & Reel	2000	4000	24000

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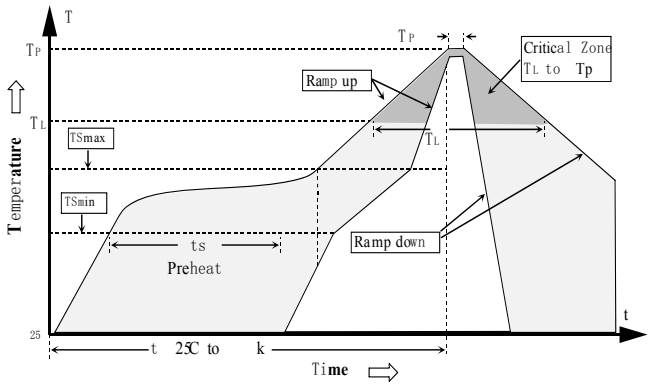
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Recommended wave soldering condition

Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

Recommended temperature profile for IR reflow



Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
Average ramp-up rate (Tsmax to Tp)	3°C/second max.	3°C/second max.
Preheat−Temperature Min (TS min) −Temperature Max (TS max) −Time(ts min to ts max)	100°C 150°C 60-120 seconds	150°C 200°C 60-180 seconds
Time maintained above: −Temperature (TL) − Time (tL)	183°C 60-150 seconds	217°C 60-150 seconds
Peak Temperature(TP)	240 +0/-5 °C	260 +0/-5 °C
Time within 5°C of actual peak temperature (tp)	10-30 seconds	20-40 seconds
Ramp down rate	6°C/second max.	6°C/second max.
Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

Note : All temperatures refer to topside of the package, measured on the package body surface.

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- When the appearance of the product and chip size does not change, in order to product the customer. quality, change the internal structure and the production process Niuhang can not notify

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Specification Revision History

Rev.	Date	Changed Items	Pre-Changed Content	Changed Content
A/1	2014-10-20	First Issue		

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